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APPLICANTS

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** CONTINUING DATA *****

This application is a DIV of 09/164,343 10/01/1998 ABN *RP yes*

** FOREIGN APPLICATIONS *****

JAPAN 9-268513 10/01/1997 *RP yes*

IF REQUIRED, FOREIGN FILING LICENSE GRANTED
** 08/20/2001

Foreign Priority claimed 35 USC 119 (a-d) conditions met	<input checked="" type="checkbox"/> yes <input type="checkbox"/> no <i>yes</i>	STATE OR COUNTRY JAPAN	SHEETS DRAWING 9	TOTAL CLAIMS 19	INDEPENDENT CLAIMS 7
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Verified and Acknowledged *[Signature]* Examiner's Signature *[Initials]* Initials

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TITLE
Semiconductor device comprising metal silicide films formed to cover gate electrode and source-drain diffusion layers and method of manufacturing the same

FILING FEE RECEIVED 1372	FEES: Authority has been given in Paper No. _____ to charge/credit DEPOSIT ACCOUNT No. _____ for following:	<input type="checkbox"/> All Fees <input type="checkbox"/> 1.16 Fees (Filing) <input type="checkbox"/> 1.17 Fees (Processing Ext. of time) <input type="checkbox"/> 1.18 Fees (Issue) <input type="checkbox"/> Other _____ <input type="checkbox"/> Credit
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RP 12-17-03

wherein the silicide on gate is thicker than on source-drain